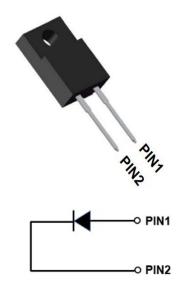




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (128°C)}	5A
Q_{c}	27nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: ITO-220AC
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112005FG1
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	٧	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _C =25°C		А	9.8
Continuous forward current @ T _C =128°C	I _F		5
Continuous forward current @ T _C =135°C			4.5
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	50
Power Dissipation@ T _C =25°C	D.	W -	33
Power Dissipation@ T _C =110°C	P _{TOT}		14
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	12.5
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.			
E	V _F	V	I _F =5A, T _j =25°C	1.41	1.6			
Forward voltage drop			I _F =5A, T _j =175°C	2.1	-			
Deverse legicare current	l _R μ/			V _R =1200V, T _j =25°C	0.5	16		
Reverse leakage current		μΑ	V _R =1200V, T _j =175°C	8	-			
Total capacitive charge	Q _C	nC	$V_R=800V, T_j=25^{\circ}C, Q_C=\int_0^{VR}C(V)dV$	27	-			
	C pF					V _R =0V, f=1MHZ	377	-
Total capacitance		pF	V _R =400V, f=1MHZ	26	-			
			V _R =800V, f=1MHZ	19	-			
Capacitance Stored Energy	Ec	μJ	V _R =800V	6.8	-			

■Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	4.5

■Typical Characteristics

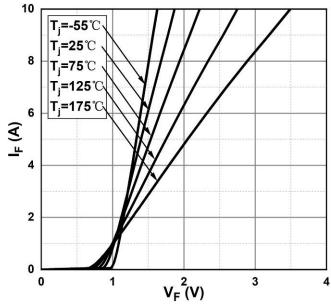


Figure 1. Forward Characteristics

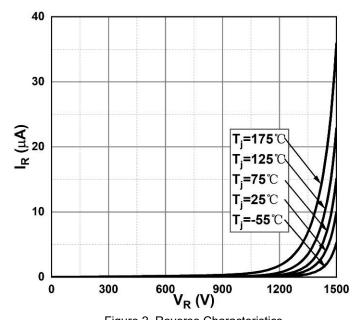
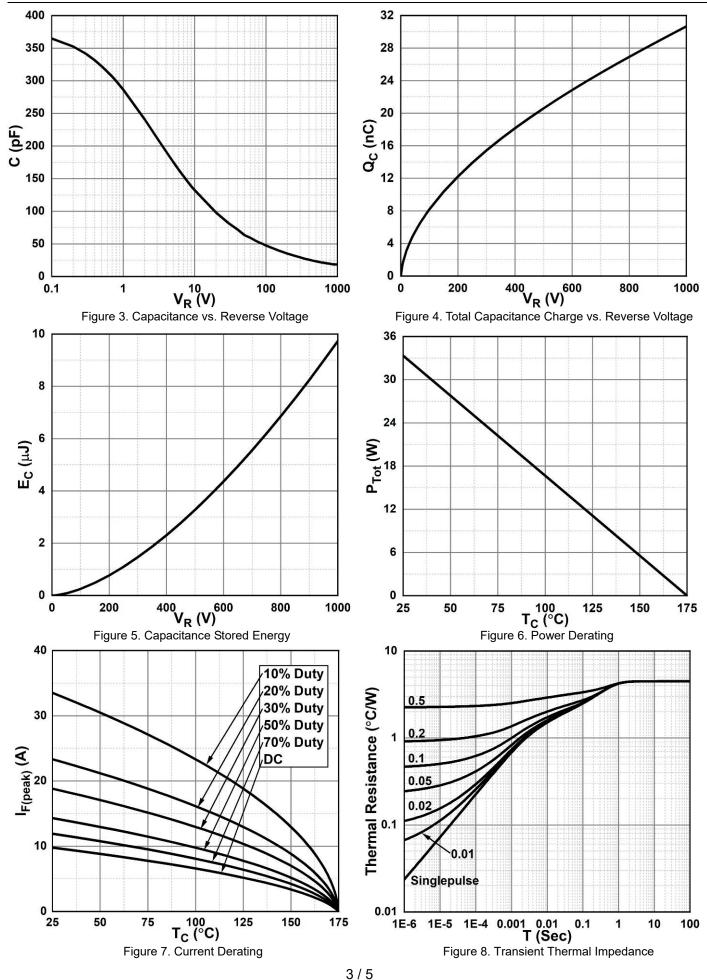


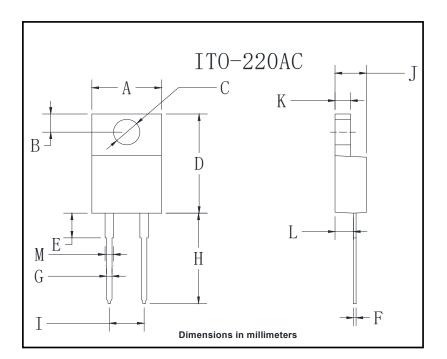
Figure 2. Reverse Characteristics







■Outline Dimensions



ITO-220AC				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
Е	3.5	4.1		
F	0.45	0.75		
G	0.45	0.75		
Н	13.35	14.15		
I	4.97	5.23		
J	4.3	4.8		
K	2.5	2.74		
L	2.58	2.82		
М	1.03	1.43		



YJD112005FG1Q



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